

XN4608

Silicon NPN epitaxial planer transistor (Tr1)
 Silicon PNP epitaxial planer transistor (Tr2)

For general amplification (Tr1)

For amplification of low frequency output (Tr2)

■ Features

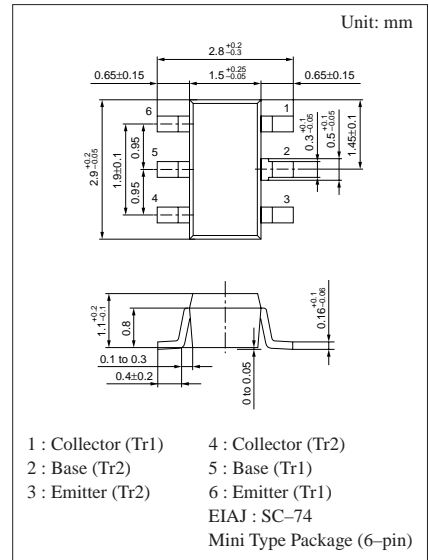
- Two elements incorporated into one package.
- Reduction of the mounting area and assembly cost by one half.

■ Basic Part Number of Element

- 2SD601A+2SB970

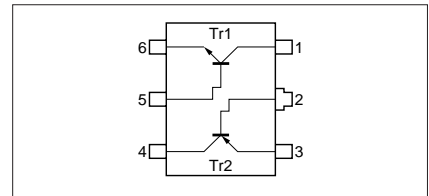
■ Absolute Maximum Ratings (Ta=25°C)

	Parameter	Symbol	Ratings	Unit
Tr1	Collector to base voltage	V_{CBO}	60	V
	Collector to emitter voltage	V_{CEO}	50	V
	Emitter to base voltage	V_{EBO}	7	V
	Collector current	I_C	100	mA
	Peak collector current	I_{CP}	200	mA
Tr2	Collector to base voltage	V_{CBO}	-15	V
	Collector to emitter voltage	V_{CEO}	-10	V
	Emitter to base voltage	V_{EBO}	-7	V
	Collector current	I_C	-0.5	A
	Peak collector current	I_{CP}	-1	A
Overall	Total power dissipation	P_T	300	mW
	Junction temperature	T_j	150	°C
	Storage temperature	T_{stg}	-55 to +150	°C



Marking Symbol: 5E

Internal Connection



■ Electrical Characteristics (Ta=25°C)

● Tr1

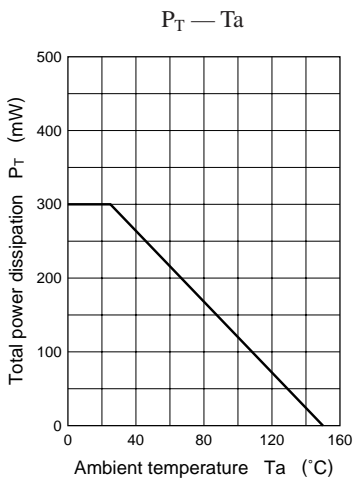
Parameter	Symbol	Conditions	min	typ	max	Unit
Collector to base voltage	V _{CBO}	I _C = 10μA, I _E = 0	60			V
Collector to emitter voltage	V _{CEO}	I _C = 2mA, I _B = 0	50			V
Emitter to base voltage	V _{EBO}	I _E = 10μA, I _C = 0	7			V
Collector cutoff current	I _{CBO}	V _{CB} = 20V, I _E = 0			0.1	μA
	I _{CEO}	V _{CE} = 10V, I _B = 0			100	μA
Forward current transfer ratio	h _{FE}	V _{CE} = 10V, I _C = 2mA	160		460	
Collector to emitter saturation voltage	V _{CE(sat)}	I _C = 100mA, I _B = 10mA		0.1	0.3	V
Transition frequency	f _T	V _{CB} = 10V, I _E = -2mA, f = 200MHz		150		MHz
Collector output capacitance	C _{ob}	V _{CB} = 10V, I _E = 0, f = 1MHz		3.5		pF

● Tr2

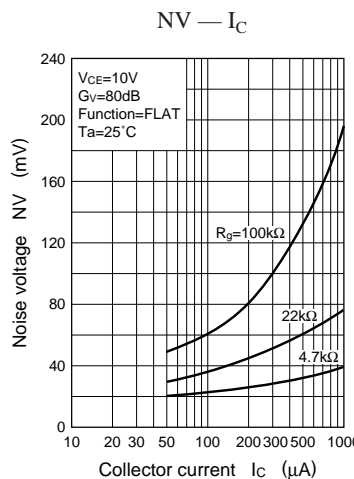
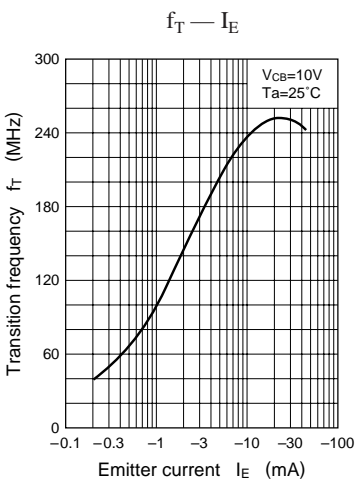
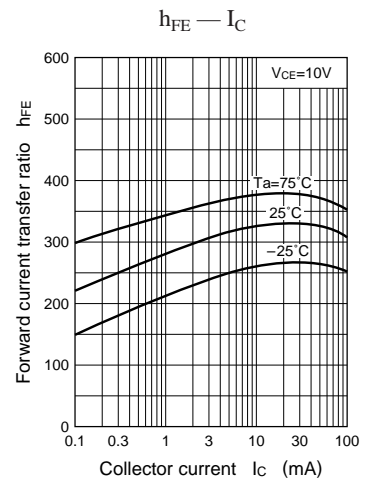
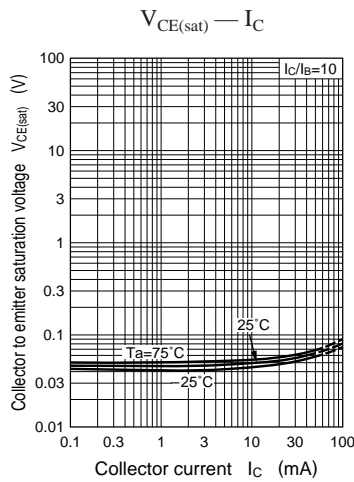
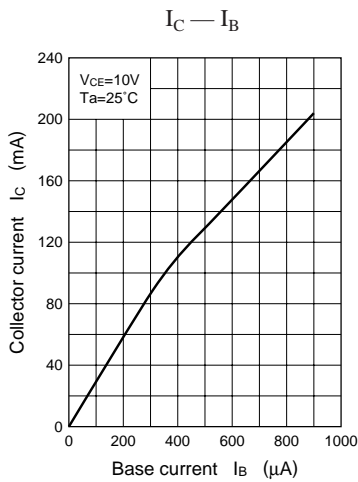
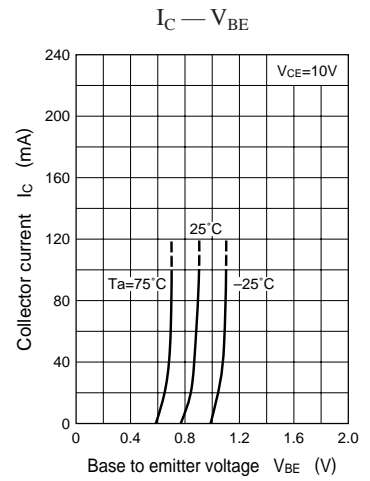
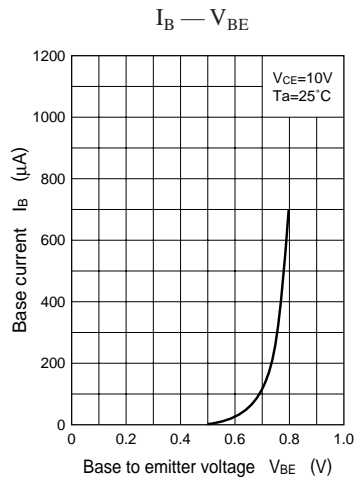
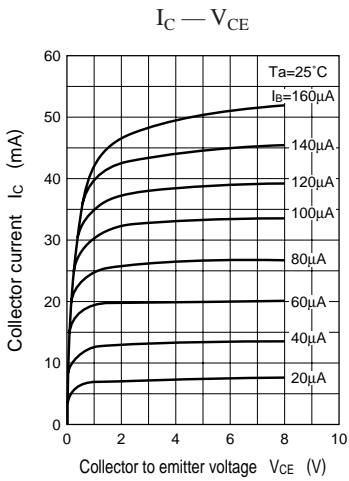
Parameter	Symbol	Conditions	min	typ	max	Unit
Collector to base voltage	V _{CBO}	I _C = -10μA, I _E = 0	-15			V
Collector to emitter voltage	V _{CEO}	I _C = -1mA, I _B = 0	-10			V
Emitter to base voltage	V _{EBO}	I _E = -10μA, I _C = 0	-7			V
Collector cutoff current	I _{CBO}	V _{CB} = -10V, I _E = 0			-0.1	μA
Forward current transfer ratio	h _{FE1}	V _{CE} = -2V, I _C = -0.5A*	100		350	
	h _{FE2}	V _{CE} = -2V, I _C = -1A*	60			
Collector to emitter saturation voltage	V _{CE(sat)}	I _C = -0.4A, I _B = -8mA		-0.16	-0.3	V
Base to emitter saturation voltage	V _{BE(sat)}	I _C = -0.4A, I _B = -8mA		-0.8	-1.2	V
Transition frequency	f _T	V _{CB} = -10V, I _E = 50mA, f = 200MHz		130		MHz
Collector output capacitance	C _{ob}	V _{CB} = -10V, I _E = 0, f = 1MHz		22		pF

* Pulse measurement

Common characteristics chart



Characteristics charts of Tr1



Characteristics charts of Tr2

